N and P-Channel Enhancement Mode Power MOSFET

Description

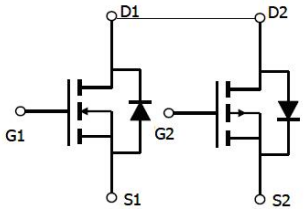
The NCE609 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge . The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

General Features

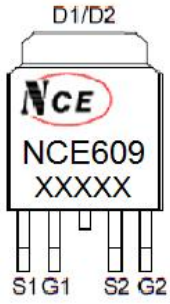
- **N-Channel**
  V_{DS} =40V,I_D =21A
  $R_{DS(ON)}$ < 17mΩ @ V_{GS}=10V
  $R_{DS(ON)}$ < 29mΩ @ V_{GS}=4.5V

- **P-Channel**
  V_{DS} =-40V,I_D = -14A
  $R_{DS(ON)}$ <32mΩ @ V_{GS}=-10V
  $R_{DS(ON)}$ < 45mΩ @ V_{GS}=-4.5V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package



Schematic diagram



Marking and pin assignment

100% UIS TESTED!

100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE609	NCE609	TO-252-4L	-	-	-

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	40	-40	V
Gate-Source Voltage		V_{GS}	±25	±25	V
Continuous Drain Current	T_C=25℃	I_D	21	-14	A
	T_C=70℃		17.5	-11.5	
Pulsed Drain Current (Note 1)		I_{DM}	84	-56	A
Maximum Power Dissipation	T_C=25℃	P_D	40	40	W
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note2)	$R_{\theta JC}$	N-Ch	3.1	℃/W
Thermal Resistance,Junction-to-Case(Note2)	$R_{\theta JC}$	P-Ch	3.1	℃/W

N-CH Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±25V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1	1.6	2.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=10A	-	14	17	mΩ
		V_{GS}=4.5V, I_D=5A	-	19	29	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=10A		15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=20V,V_{GS}=0V, F=1.0MHz	-	1110	-	PF
Output Capacitance	C_{oss}		-	114	-	PF
Reverse Transfer Capacitance	C_{rss}		-	109	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=20V, R_L=2Ω V_{GS}=10V,R_{GEN}=3Ω	-	4	-	nS
Turn-on Rise Time	t_r		-	11.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	18	-	nS
Turn-Off Fall Time	t_f		-	5.6	-	nS
Total Gate Charge	Q_g	V_{DS}=20V,I_D=10A, V_{GS}=10V	-	30	-	nC
Gate-Source Charge	Q_{gs}		-	5	-	nC
Gate-Drain Charge	Q_{gd}		-	7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=10A	-	0.8	1.2	V

P-CH Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-40V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±25V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.0	-1.6	-2.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-7A	-	27	32	mΩ
		V_{GS}=-4.5V, I_D=-4A	-	34	45	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-7A	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-20V,V_{GS}=0V, F=1.0MHz	-	1139	-	PF
Output Capacitance	C_{oss}		-	114	-	PF
Reverse Transfer Capacitance	C_{rss}		-	103	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-20V, R_L=2.3Ω V_{GS}=-10V,R_{GEN}=6Ω	-	10	-	nS
Turn-on Rise Time	t_r		-	15	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	t_f		-	18	-	nS
Total Gate Charge	Q_g	V_{DS}=-20V,I_D=-7A V_{GS}=-10V	-	22.5	-	nC
Gate-Source Charge	Q_{gs}		-	2.4	-	nC
Gate-Drain Charge	Q_{gd}		-	5.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-14A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

N- Channel Typical Electrical and Thermal Characteristics (Curves)

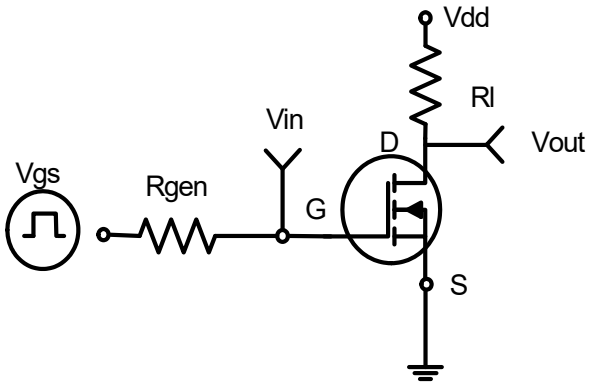


Figure 1:Switching Test Circuit

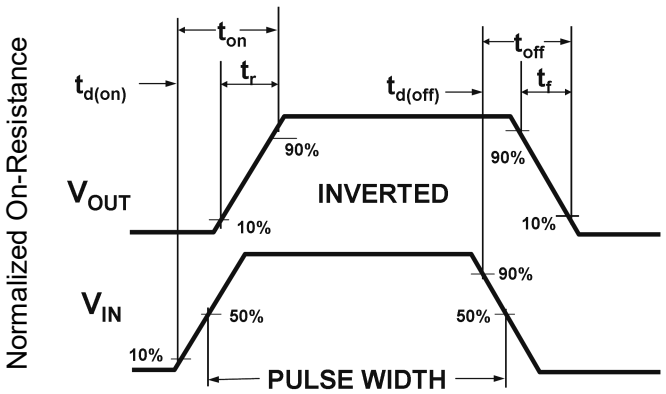
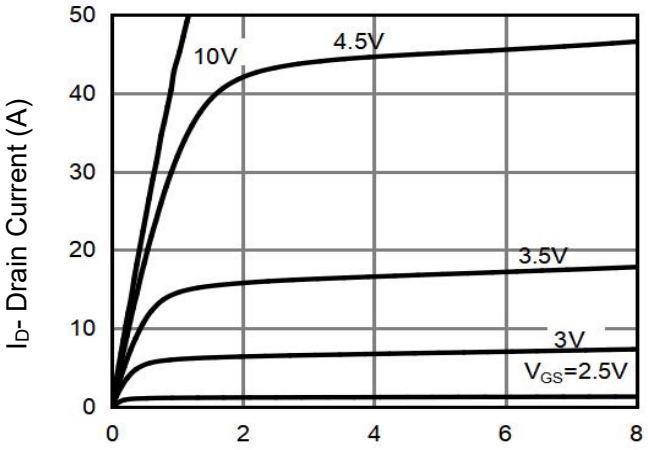
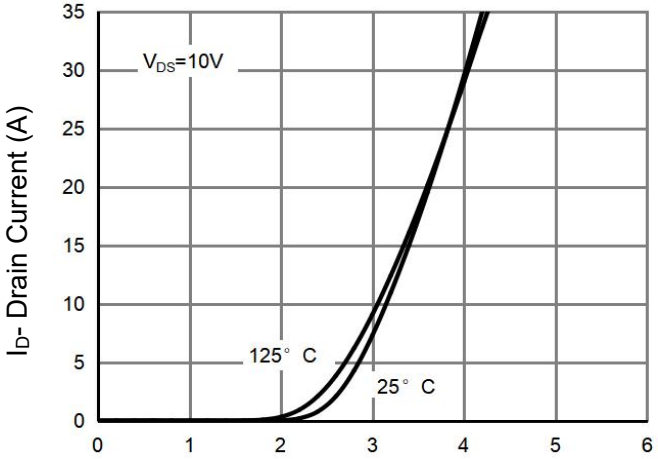


Figure 2:Switching Waveforms



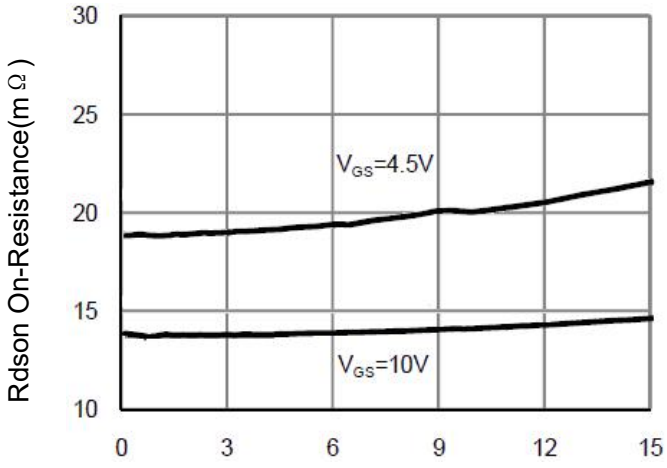
Vds Drain-Source Voltage (V)

Figure 3 Output Characteristics



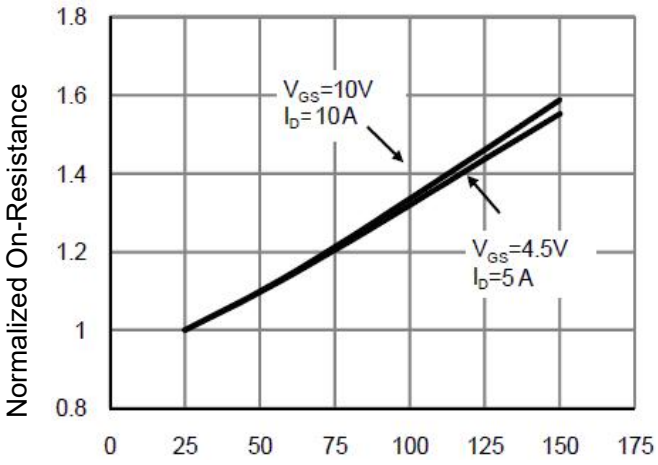
Vgs Gate-Source Voltage (V)

Figure 4 Transfer Characteristics



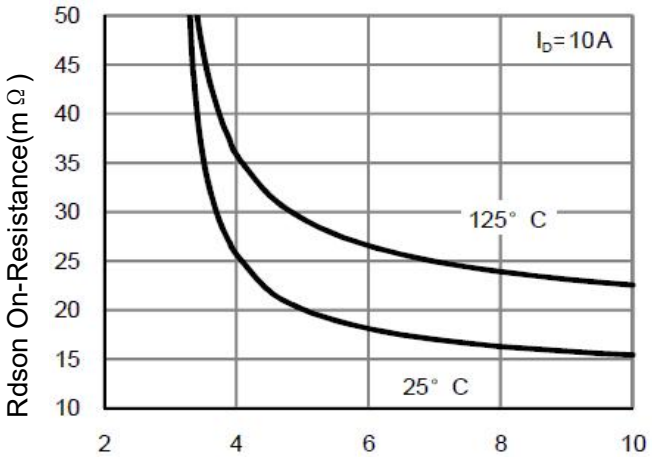
I_D- Drain Current (A)

Figure 5 Drain-Source On-Resistance



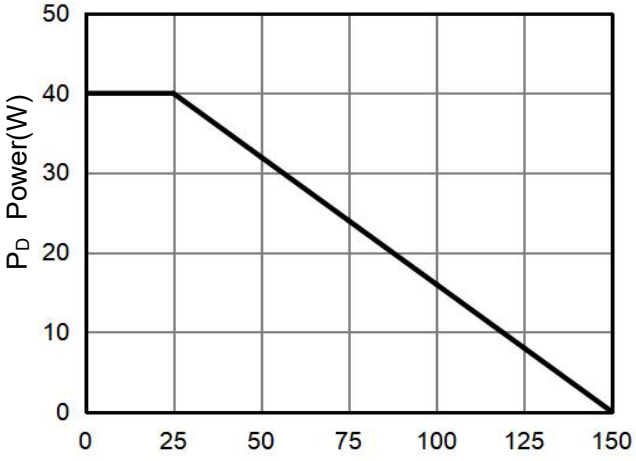
T_J-Junction Temperature(℃)

Figure 6 Drain-Source On-Resistance



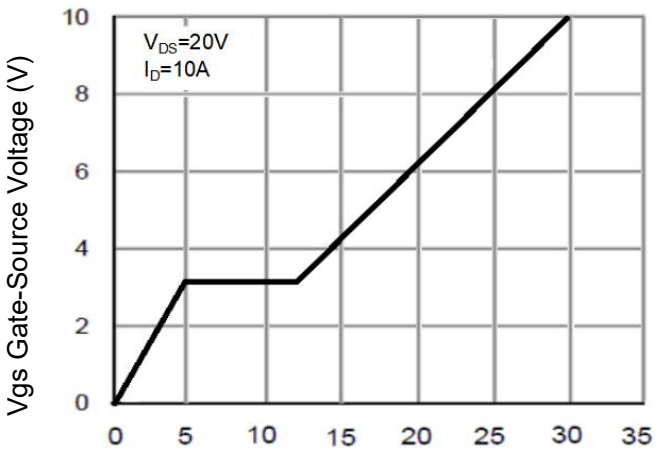
Vgs Gate-Source Voltage (V)

Figure7 Rdson vs Vgs



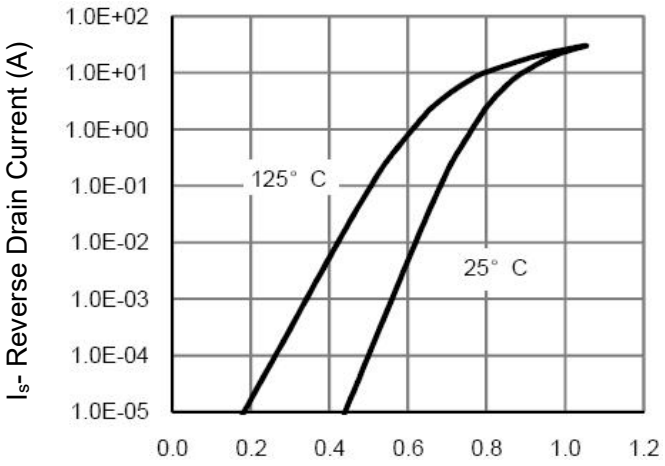
T_J-Junction Temperature(℃)

Figure 8 Power Dissipation



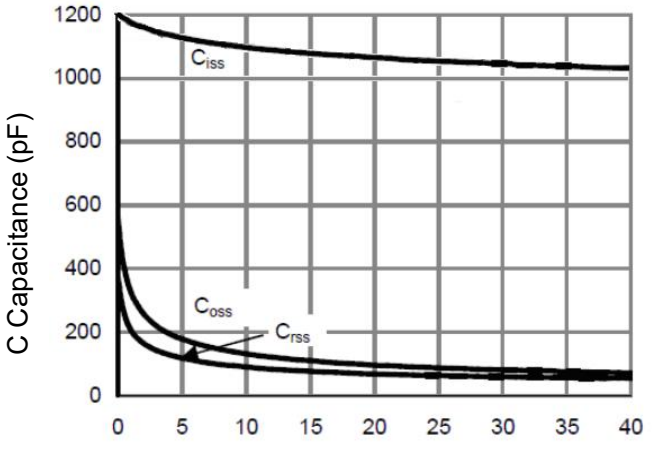
Qg Gate Charge (nC)

Figure 9 Gate Charge



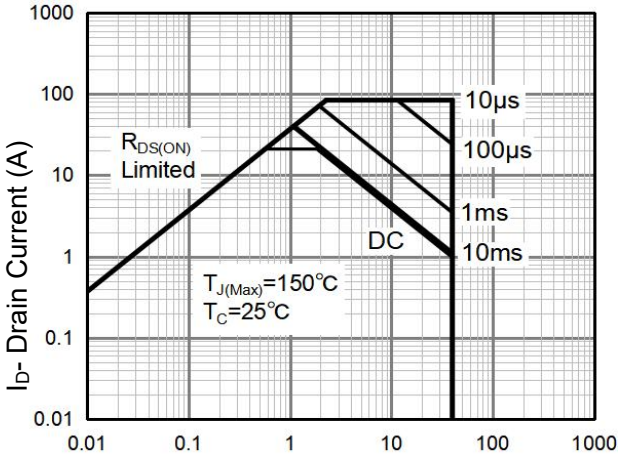
Vds Drain-Source Voltage (V)

Figure 10 Source- Drain Diode Forward



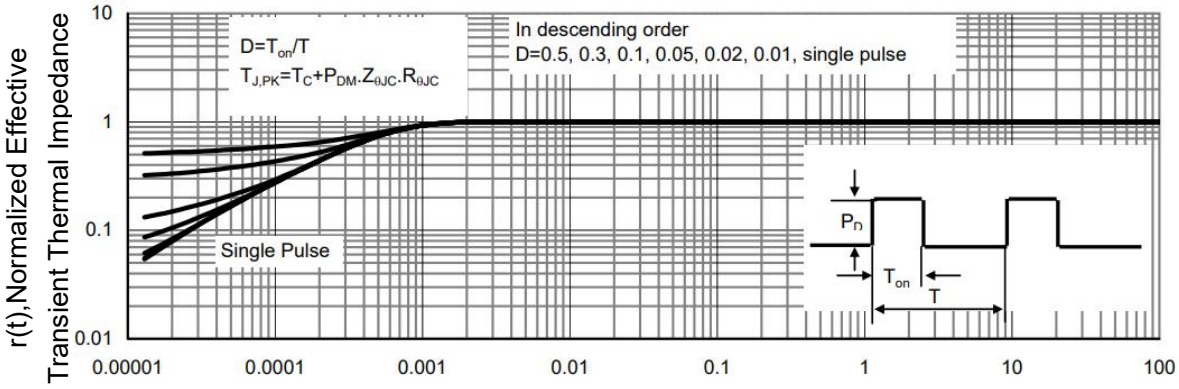
Vds Drain-Source Voltage (V)

Figure 11 Capacitance vs Vds



Vds Drain-Source Voltage (V)

Figure 12 Safe Operation Area



Square Wave Pluse Duration(sec)

Figure 13 Normalized Maximum Transient Thermal Impedance

P- Channel Typical Electrical and Thermal Characteristics (Curves)

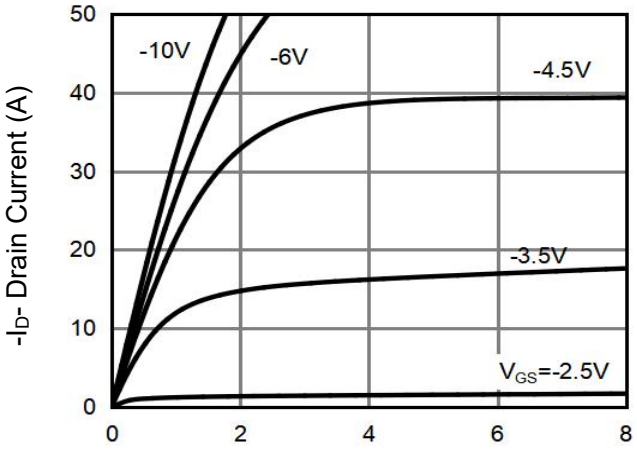


Figure 1 Output Characteristics

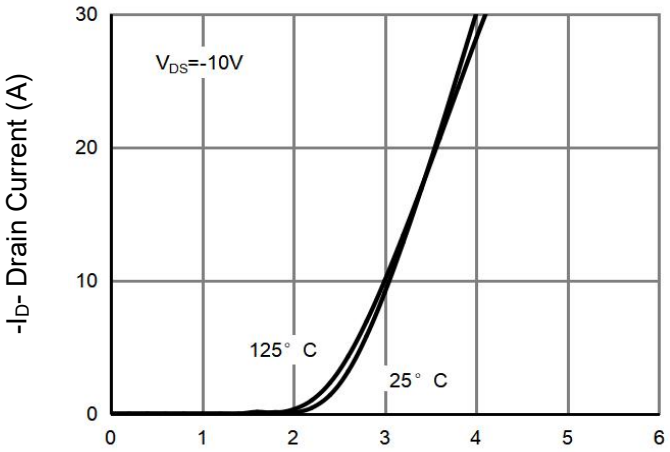


Figure 2 Transfer Characteristics

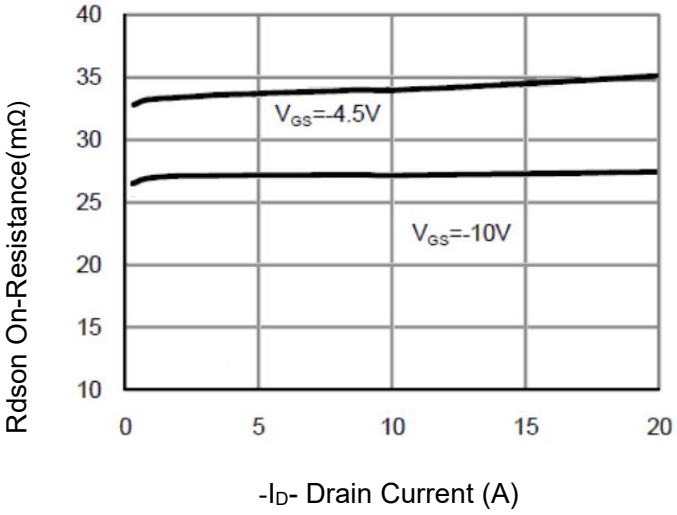


Figure 3 Rdson- Drain Current

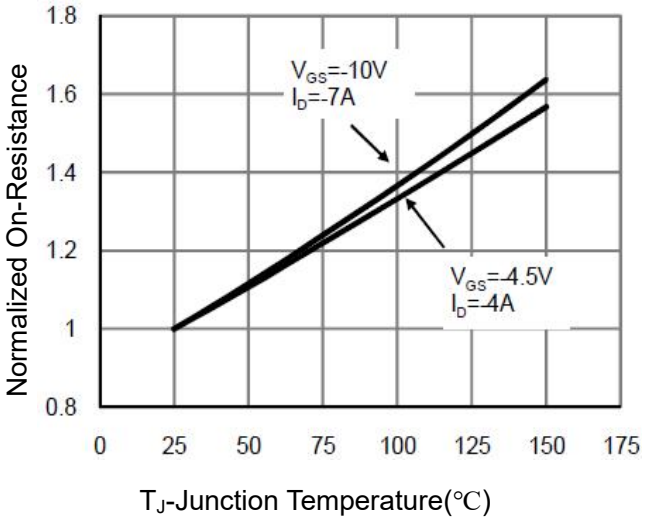


Figure 4 Rdson-Junction Temperature

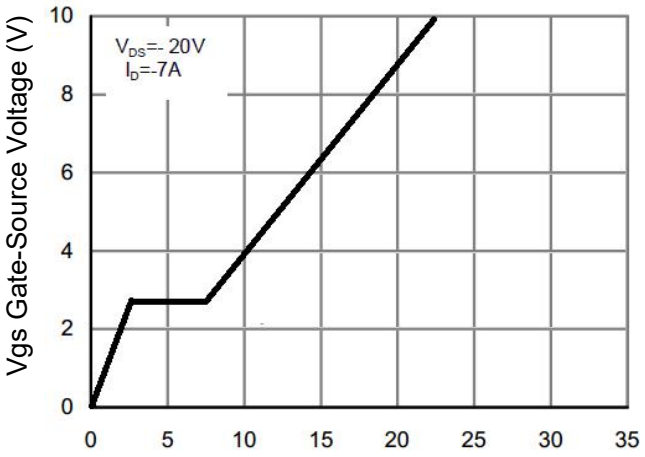


Figure 5 Gate Charge

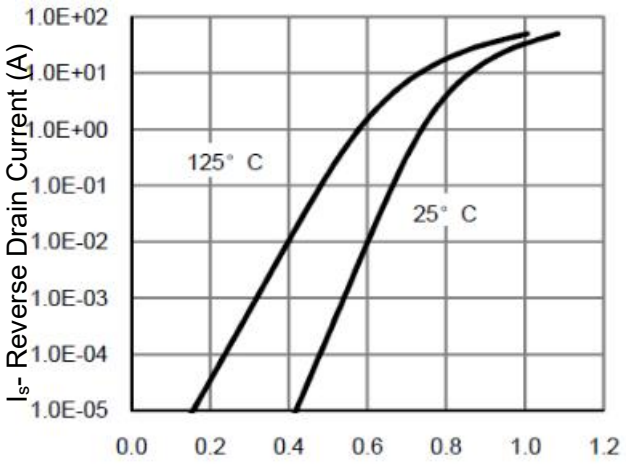


Figure 6 Source- Drain Diode Forward

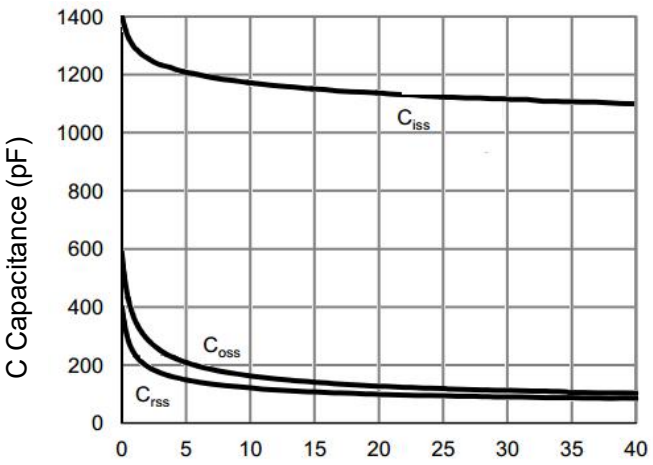


Figure 7 Capacitance vs Vds

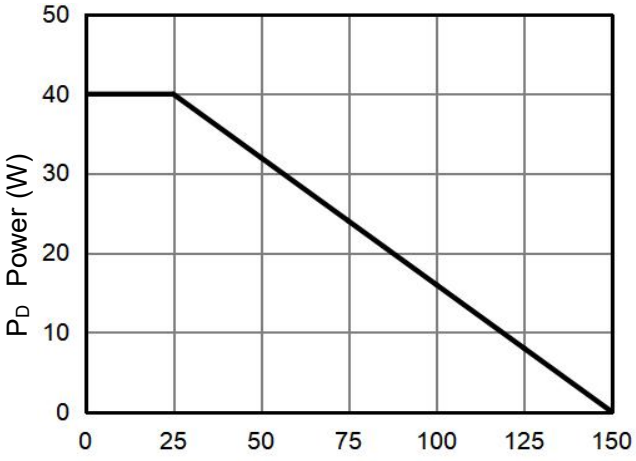


Figure 9 Power Dissipation

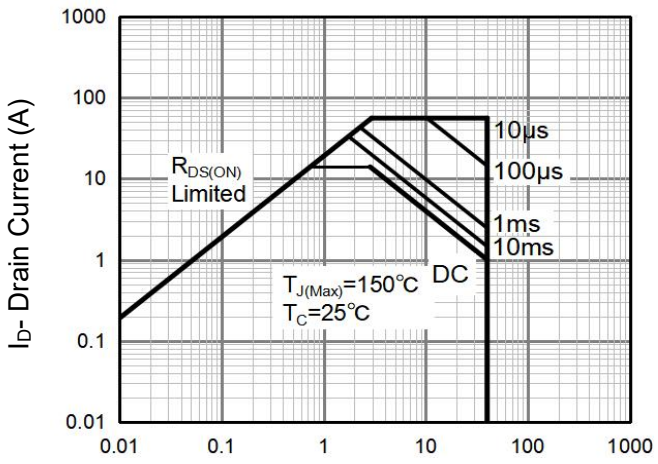


Figure 8 Safe Operation Area

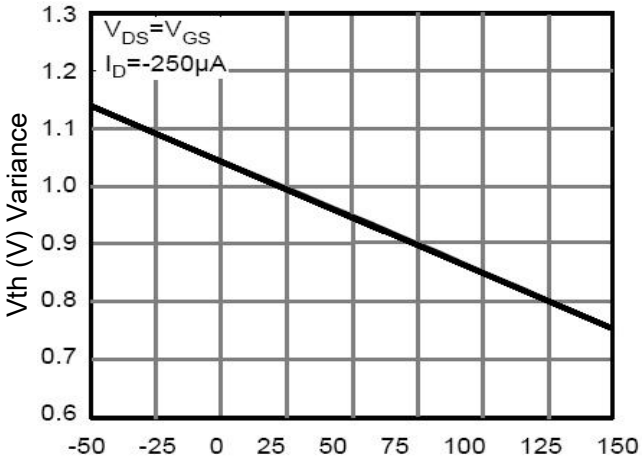


Figure 10 $V_{GS(th)}$ vs Junction Temperature

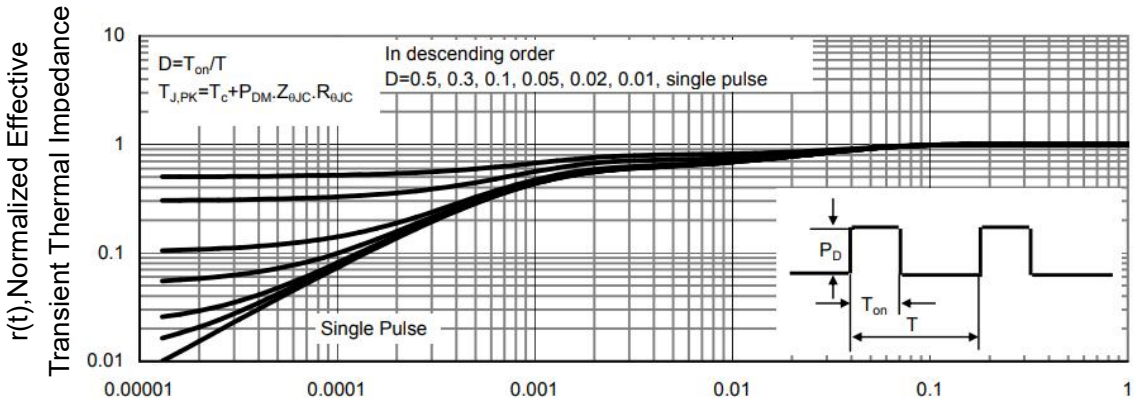
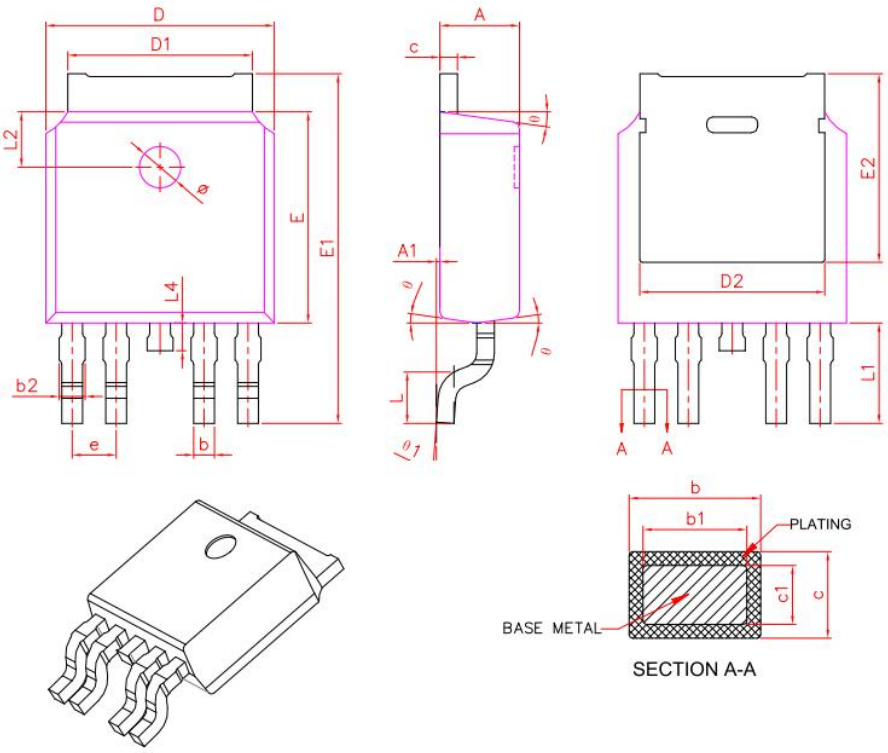


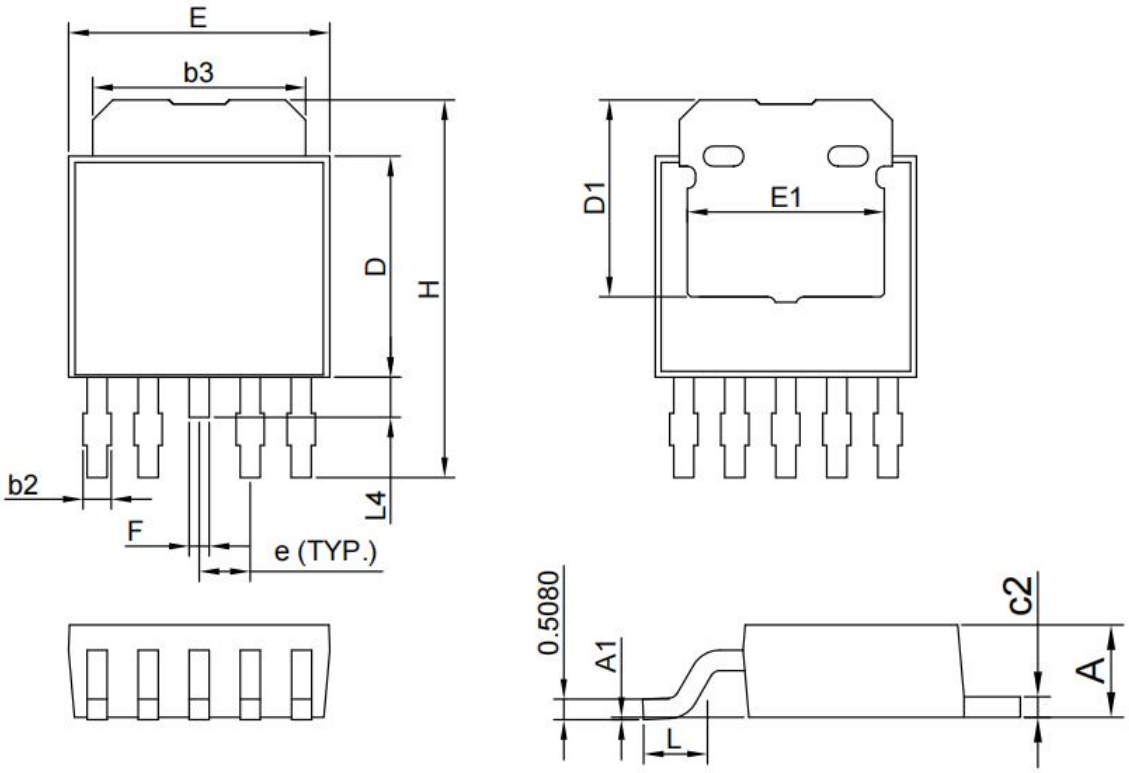
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-4L (E) Package Information



TO252-4L			
DIM.	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	0.00	0.08	0.13
b	0.50	0.60	0.70
b1	0.57	0.60	0.63
b2		0.75REF	
c	0.46	0.508	0.58
c1	0.50	0.508	0.52
D	6.50	6.60	6.70
D1	5.10	5.334	5.46
D2		5.346REF	
E	6.00	6.10	6.20
E1	9.80	10.10	10.40
E2		5.446REF	
e	1.17	1.27	1.37
L	1.40	1.50	1.70
L1		2.90REF	
L2		1.60REF	
L4	0.60	0.80	1.00
ø	ø1.10	ø1.20	ø1.30
Θ	5°	8°	10°
Θ1	0°	–	8°
All dimensions in millimeters			

TO-252-4L (X) Package Information



COMMON DIMENSIONS

UNITS OF MEASURE=MILLIMETER

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	0.08	0.15
b	0.45	0.53	0.60
b2	0.50	0.65	0.80
b3	5.20	5.35	5.50
c2	0.45	0.50	0.55
D	5.40	5.60	5.80
D1	4.57	–	–
E	6.40	6.60	6.80
E1	3.81	–	–
e	1.27 REF.		
F	0.40	0.50	0.60
H	9.40	9.80	10.20
L	1.40	1.59	1.77
L1	2.40	2.70	3.00
L2	0.80	1.00	1.20

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